

N-Channel 600V MOSFET

Description

The MSF7N60 is a N-channel enhancement-mode MOSFET, providing the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost effectiveness. The ITO-220AB package is universally preferred for all commercial-industrial applications

Features

- Low On Resistance •
- Simple Drive Requirement •
- Low Gate Charge •
- Fast Switching Characteristic
- RoHS compliant package ٠

Application

- **Open Framed Power Supply**
- Adapter •
- STB •

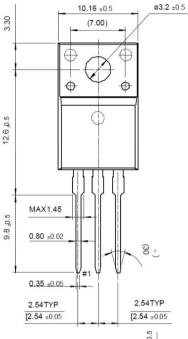
Package type : ITO220-AB

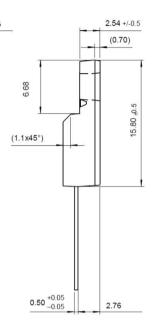
Packing & Order Information

50/Tube ; 1,000/Box



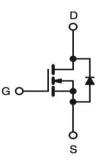








Graphic symbol



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings					
Symbol	Parameter	Value	Unit		
V _{DSS}	Drain-Source Voltage	600	V		
V _{GS}	Gate-Source Voltage	±30	V		
т	Drain Current -Continuous (TC=25°C)	7.0	А		
ID	Drain Current -Continuous (TC=100°C)	4.4	А		
I _{DM}	Drain Current Pulsed	21	А		
E _{AS}	Single Pulsed Avalanche Energy	48	mJ		
IAR	Avalanche Current	7.0	А		



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Absolute Maximum Ratings						
Symbol	Parameter	Value	Unit			
EAR	Repetitive Avalanche Energy	3.1	mJ			
dv/dt	Peak Diode Recovery dv/dt	4.5	V/ns			
D	Total Power Dissipation (TC = 25 °C)	31	W			
PD	Derating Factor above 25 °C	0.25	W/°C			
T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C			
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 10 seconds	300	°C			
TPKG	Maximum Temperature for Soldering @ Package Body for 10 seconds	260	°C			
TJ	Storage Temperature	150	°C			

Note:

1.Repetitive rating; pulse width limited by maximum junction temperature.

- 2. IAS \leq 7A, V_{DD}=50V, L=7mH, V_G=10V, starting TJ=+25°C.
- 3. I_{SD} ≤7A, dI/dt≤200A/µs, VDD≤BVDSS, starting TJ=+25°C.

Thermal characteristics						
Symbol	Parameter	Max.	Units			
$R_{\theta J}c$	Junction-to-Case	2.6	°C/W			
Roja	Junction-to-Ambient	62.5	C/W			

Off Characteristi	cs				
Symbol	Test Conditions	Min	Typ.	Max.	Units
$V_{GS(th)}$	$V_{\rm DS}=V_{\rm GS},\ I_D{=}250\mu A$	2.0		4.0	v
*R _{DS(ON)}	$V_{GS}=10\ V$, $I_{D}=3.5\ A$		0.85	1.2	Ω
BV _{DSS}	$V_{GS}=0~V~,~I_D=250\mu A$	600			V
$\Delta BV_{DSS}/\Delta T_J$	$I_D\!=\!250\mu A,$ Referenced to $25^{\circ}\mathrm{C}$		0.6		V/°C
I _{DSS}	$\label{eq:VDS} \begin{split} V_{DS} &= 600 \ V \mbox{, } V_{GS} = 0 \ V \\ V_{DS} &= 480 \ V \mbox{, } V_{C} = 125^{\circ} C \end{split}$			1 10	uA
I _{GSS}	$V_{GS} = \pm 30$			±100	nA

Dynamic Cha	racteristics				
Symbol	Test Conditions	Min	Typ.	Max.	Units
CISS			1482		pF
Coss	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		121.7		pF
C _{RSS}			14		pF



N-Channel 600V MOSFET

Dynamic Characteristics					
Symbol	Test Conditions	Min	Typ.	Max.	Units
Qg			28	37	nC
Qgs	$V_{DG} = 300 \text{ V}, \text{I}_D = 7 \text{ A},$ 		4.7		nC
Q _{gd}	VGS = 10 V		11		nC
t _{d(on)}			10	30	ns
t _r			35	80	ns
t _{d(off)}			45	100	ns
tf			40	90	ns

Dynamic Cha	uracteris tics				
Symbol	Test Conditions	Min	Typ.	Max.	Units
CISS			1500	2010	pF
Coss	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0MHz		145	190	pF
Crss			13	20	pF

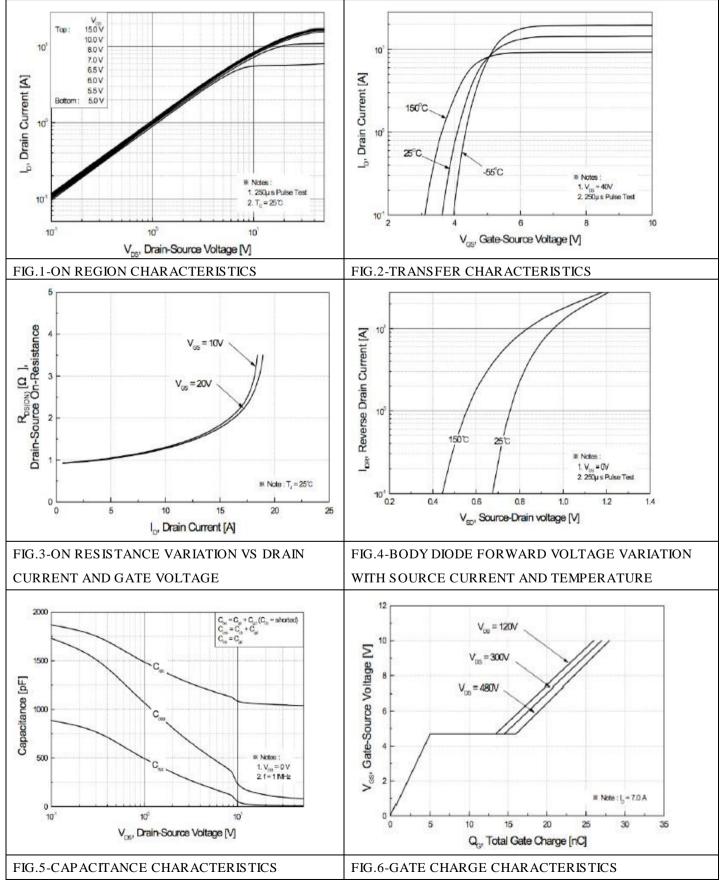
Source-Drain Diode Characteristics					
Symbol	Test Conditions	Min	Typ.	Max.	Units
Is	$V_G = V_D = 0$			7	
I _{SM}	$V_S = 13 V$			28	A
V _{SD}	$I_S = 7 \text{ A}, V_{GS} = 0 \text{ V}$			1.4	V
trr			350		ns
Qrr	$I_F = 7 \text{ A}, V_{GS} = 0 \text{ V}, \text{dIF/dt=100A/}\mu\text{s}$		3.3		uC

*Pulse Test : Pulse Width ≤300µs, Duty Cycle≤2%



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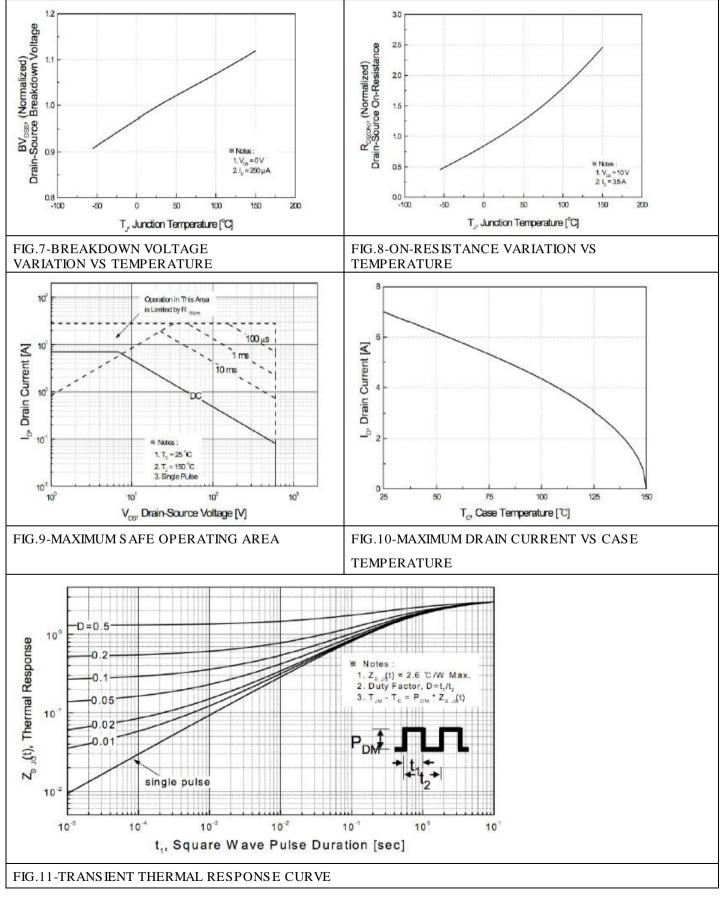
Characteristics Curve





N-Channel 600V MOSFET

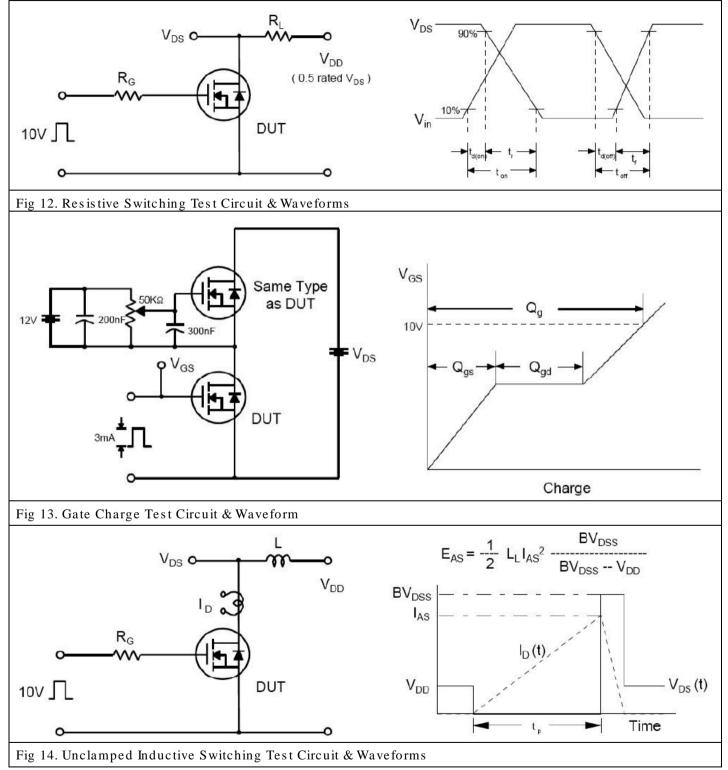
Characteristics Curve





N-Channel 600V MOSFET

Characteristics Test Circuit & Waveform





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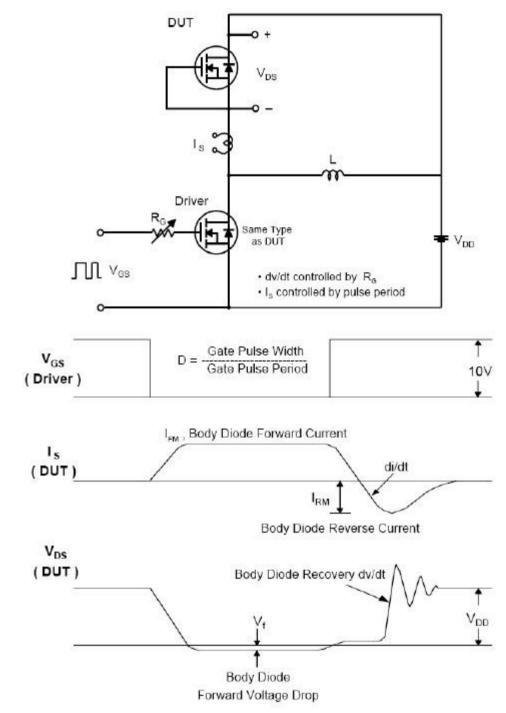


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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